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November 2013

FDP020N06B

N-Channel PowerTrench[®] MOSFET 60 V, 313 A, 2 m Ω

Features

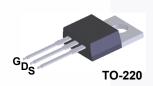
- $R_{DS(on)}$ = 1.65 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 100 A
- Low FOM R_{DS(on)} * Q_G
- Low Reverse-Recovery Charge, Q_{rr} = 194 nC
- · Soft Reverse-Recovery Body Diode
- Enables High Efficiency in Synchronous Rectification
- · Fast Switching Speed
- · 100% UIL Tested
- RoHS Compliant

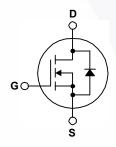
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- Renewable System





Absolute Maximum Ratings T_C = 25°C unless otherwise noteed.

Symbol		Parameter	FDP020N06B_F102	Unit
V_{DSS}	Drain to Source Voltage	60	V	
V_{GSS}	Gate to Source Voltage		±20	V
		- Continuous (T _C = 25°C, Silicon Limited)	313*	
I _D	Drain Current	- Continuous (T _C = 100°C, Silicon Limited)	221*	Α
		- Continuous (T _C = 25°C, Package Limited)	120	
I _{DM}	Drain Current	- Pulsed (Note 1)	1252	Α
E _{AS}	Single Pulsed Avalanche	1859	mJ	
dv/dt	Peak Diode Recovery dv	/dt (Note 3)	6.0	V/ns
D	Power Dissipation	(T _C = 25°C)	333	W
Power Dissipation		- Derate Above 25°C	2.2	W/°C
T _J , T _{STG}	Operating and Storage T	-55 to +175	οС	
T _L	Maximum Lead Tempera	ture for Soldering, 1/8" from Case for 5 Seconds	300	οС

^{*} Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	FDP020N06B_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	-0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP020N06B_F102	FDP020N06B	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	60	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.03	-	V/°C
	Zero Gate Voltage Drain Current	V _{DS} = 48 V, V _{GS} = 0 V	-	-	1	
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 48 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	3.3	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 100 A	-	1.65	2.0	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 100 A	-	263	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	.,	-	16100	20930	pF	
C _{oss}	Output Capacitance	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		-	3840	4992	pF
C _{rss}	Reverse Transfer Capacitance			-\	127	-	pF
C _{oss(er)}	Energy Related Output Capacitance	V _{DS} = 30 V, V _{GS} = 0 V		- \	5897	-	pF
Q _{g(tot)}	Total Gate Charge at 10V			-	206	268	nC
Q_{gs}	Gate to Source Gate Charge	V _{DS} = 30 V, I _D = 100 A,	•	-	87	-	nC
Q _{gs2}	Gate to Threshold to Plateau	V _{GS} = 10 V	•	-	36	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	34	-	nC
ESR	Equivalent Series Resistance(G-S)	f = 1 MHz		-	0.9	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	74	158	ns
t _r	Turn-On Rise Time	$V_{DD} = 30 \text{ V}, I_D = 100 \text{ A},$	-/	62	134	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 4.7 Ω	-	112	234	ns
t _f	Turn-Off Fall Time	(Note 4)	/ -	42	94	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	313*	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	1252	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 100 A	-	-	1.25	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, V_{DD} = 30 \text{ V}, I_{SD} = 100 \text{ A},$	-	106	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	194	-	nC

- 1: Repetitive rating: pulse-width limited by maximum junction temperature
- 2: Starting $T_J = 25^{\circ}C$, L = 3 mH, $I_{AS} = 35.2$ A
- 3: I_{SD} ≤ 100 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C
 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

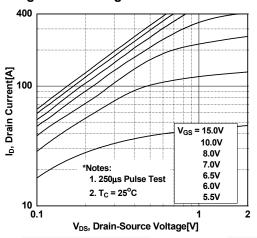


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

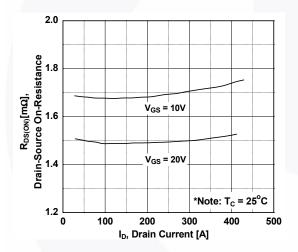


Figure 5. Capacitance Characteristics

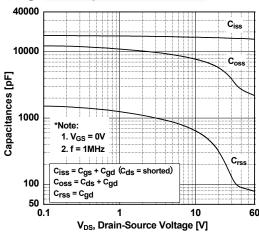


Figure 2. Transfer Characteristics

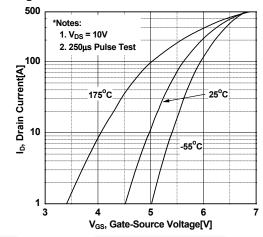


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

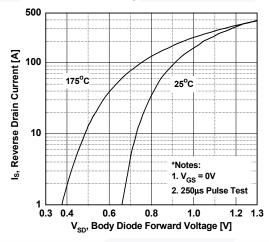
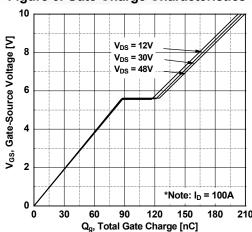


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

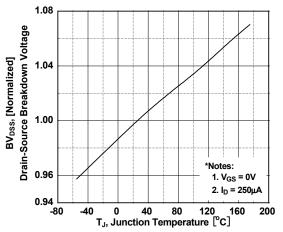


Figure 9. Maximum Safe Operating Area

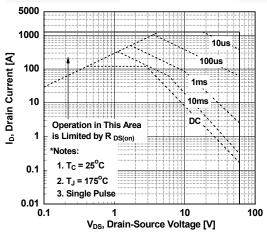


Figure 11. Unclamped Inductive Switching Capability

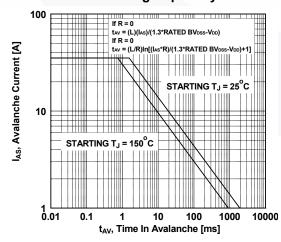


Figure 8. On-Resistance Varition vs. Temperature

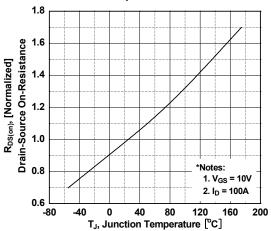


Figure 10. Maximum Drain Current vs. Case Temperature

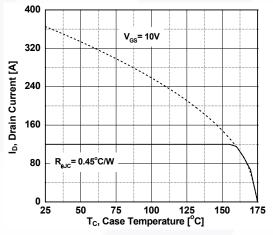
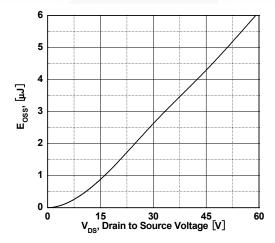
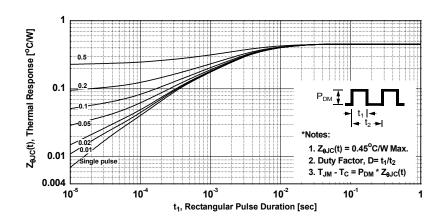


Figure 12. Eoss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve



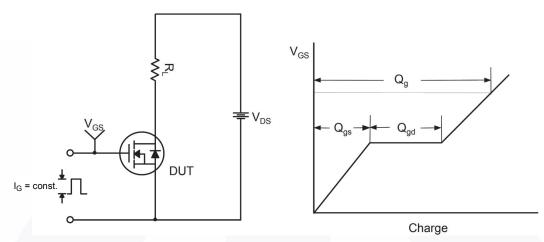


Figure 14. Gate Charge Test Circuit & Waveform

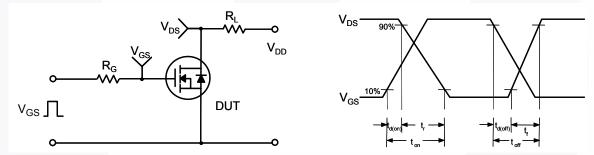


Figure 15. Resistive Switching Test Circuit & Waveforms

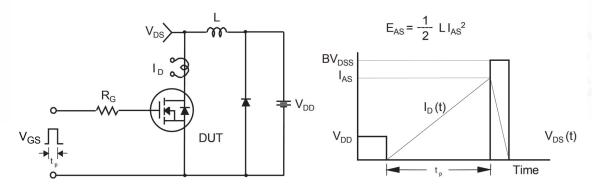


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

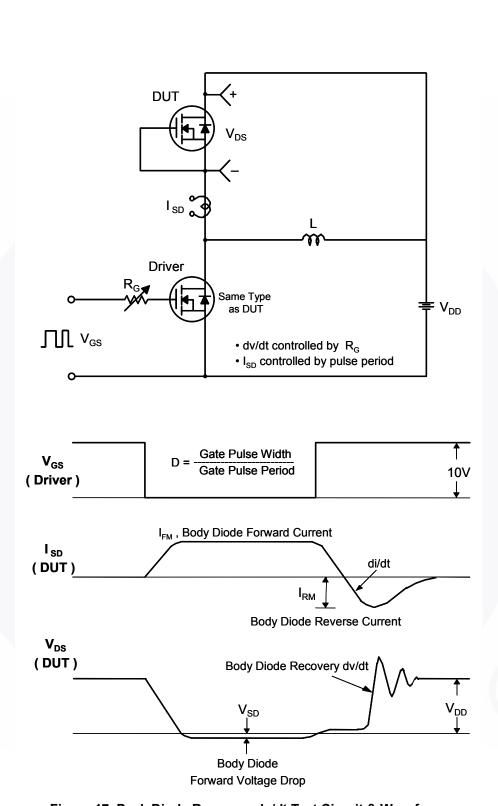


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

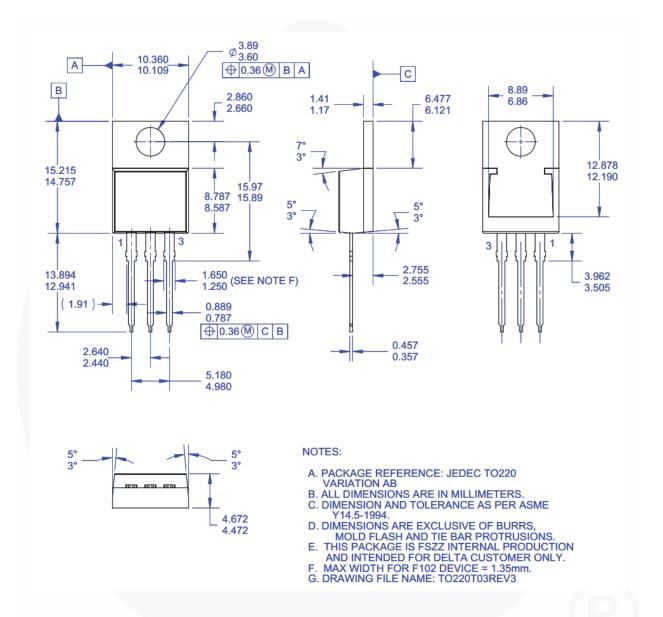


Figure 18. TO-220, Molded, 3-Lead, Jedec Variation AB (Delta)

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Rev 166

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